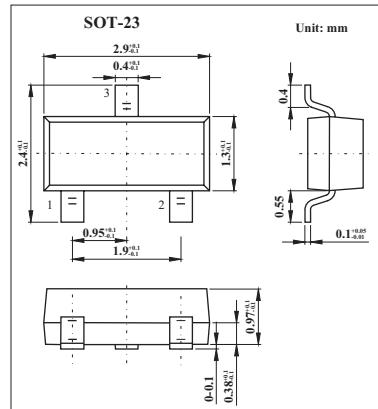


Schottky barrier diode

1PS59SB21

■ Features

- Ultra fast switching speed
- Low forward voltage
- Guard ring protected
- Small SMD package.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Min	Max	Unit
Continuous reverse voltage	V _R		40	V
Continuous forward current	I _F		200	mA
Non-repetitive peak forward current	I _{FSM}		1	A
Storage temperature	T _{stg}	-65	+150	°C
Junction temperature	T _j		125	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Max	Unit
forward voltage	V _F	I _F = 10 mA		300	mV
		I _F = 100 mA		420	
		I _F = 200 mA		550	
reverse current	I _R	V _R = 35 V		15	μ A
		V _R = 35 V, T _j = 100 °C, note 1		3	mA
diode capacitance	C _d	f = 1 MHz; V _R = 0 V	40	50	pF
thermal resistance from junction to ambient	R _{th j-a}			500	K/W

Note

1. Pulse test: tp = 300 μ s; δ = 0.02.

■ Marking

Marking	21
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